



Analog Mixed Signal

Reliability Report

Revision E
October 2016

Table of Contents

1.0	Reliability Program Overview	--	03
2.0	Product Portfolio	--	04
3.0	Accelerated Reliability Testing	--	05
3.1	FIT Rate Calculation and Assumptions	--	05
4.0	Silicon Reliability Summary	--	06
4.1	ESD Summary	--	07
5.0	Non Volatile Reliability Summary	--	09
6.0	Package Reliability Summary	--	10
6.1	Package Level	--	10
6.2	Product Level	--	15
7.0	Revision Summary	--	23

1.0 Reliability Program Overview

Reliability is defined as product performance to specification over time in response to varied (specified) environmental stress conditions.

The reliability function “R(t)” indicates the ratio of the conforming products that can function properly when the time “t” elapses after starting use.

Microsemi - AMS publishes this report to provide customers with the intent to notify about the reliability of our product portfolio.

Some of the important features of our program are,

- Product qualifications are performed per internal procedures aligned to the industry standards mentioned above.
- Product reliability is measured periodically to ensure that the product performance meets or exceeds requirements.
- Reliability tests are executed in response to internal requirements.
- Report is published annually.

1.1 Qualification

Reliability tests used in the qualification of new devices (wafer process and package) are designed to ensure that Microsemi – AMS’s products satisfy applicable industry standards as part of new product introduction process. Products are required to be qualified based on applicable following standards before they are released to production,

- Automotive products -- AECQ100
- Commercial products -- JEDEC
- Hi Reliability/Space products -- MIL PRF 38535
(Applicable test methods from MIL STD 883 for QML Q & V)

1.2 Ongoing Reliability Monitor (ORM) Program

- The reliability monitor program is based on the maturity of the wafer process, existing data (tied to the number of device hours, FIT rate) and current run rate.
- Reliability data shown in this report is based on products/product families (based upon the same logic elements, embedded storage elements, interconnect technology, etc).
- Product families are qualified based upon the internal requirements and usually include products with a range of densities, package types, and package lead counts.
- The tests used as part of ORM test suite are determined per internal requirements.
- Units that are planned for ORM use are tested using production test equipment to data sheet limits before being stressed. Post test measurements are also done on the same production test equipment to data sheet limits. Any unit that does not meet the data sheet specification is considered a reject.

2.0 Product Portfolio

Microsemi AMS Group's products are categorized primarily into the following product families,

Product Family	Product/Product Family
Sensors	AA 51X, AA 54X, AA 55X, AA 56X, AA 57X, AA58X, AA 61X, AA66X, AAP 1XX, AAP 2XX, AAP 6XX & AAP 8XX
	LX 19XX & LX 33XX
	P 31X
Backlighting	AAC 2XX, AA 6XX & AA 7XX
	LX 22XXX, LX 24XXX, LX 27XXX & LX 95XX
	LXE 19XX, LXM16XX, LXMG 19XX & 22XX
	SGE 13XXX, SGE 23XX, SGE 24XX & SGE 25XX
Hi Rel	AAHS2XX & AA7XX/AA7XX
	LX 45XX & LX 77XX
	SG 07XXX, SG 109X, SG 117XXX, SG 120 XXX, SG 137 XXX, SG 140 XXX, SG 143 XXX, SG150 XXX, SG15XX XXX, SG16XX XXX, SG 17XX XXX, SG 18XX XXX, SG 20XX XXX, SG 22XX XXX, SG 28XX XXX, SG 32XX, SG 35 XX, SG55XX XXX, SG 7XX XXX, SG 78XX XXX & SG 79XX XXX
	SGR 11X XXX & SGR 18XX XXX
	UC 18XXXX & UC 28XXXX
	UC 18XXXX & UC 28XXXX
Power Management	AAX 2XX
	IPS 10XX, IPS 18XX & IPS 21X
	LX12 XXX, LX16 XX, LX 17XX, LX 18XX, LX 22XX, LX 24XX & LX 27XX, LX 71XX, LX 73XX, LX 82XX, LX 83XX, LX 85XX & LX 95XX
	LXE 16XX, LXE 17XX, LXE 18XX, LXE 9XXX, NX 2XXX, NX 4XXX, NX 7XXX & NX 9XXX
	SG 2XXX, SG 3XXX & SG 7XXX
	UC 28XXX & UC 38XXX

3.0 Accelerated Reliability Testing

Microsemi AMS Group performs accelerated testing to assess reliability of its devices,

- Overstresses are used to produce the same failure mechanisms that would be seen under normal conditions but in a much shorter period of time.
- Acceleration factors (Temperature and Voltage) are used by Microsemi AMS to estimate failure rates based on the results of accelerated testing.
- The objective of accelerated testing is to identify the failure mechanisms and eliminate them as a cause of failure during the useful life of our products.

3.1 FIT Rate Calculation and Assumptions

Microsemi uses exponential distribution of failures in time and predicts constant failure rate at operating conditions,

- Extrapolation uses thermal and voltage acceleration factors based on JEDEC formulas (JEP122).
- FIT rate is calculated using JESD85 (Methods for Calculating Failure Rates in Units of FITs) standard.
- All of the FIT (Failure in Time) rate and MTTF (Mean Time to Failure) numbers reported here use a base set of assumptions.
 - The failure rate is calculated using Chi-square distribution at 60% confidence interval from the small number of failures and limited sample size of the population tested.
 - The Chi-squared value is calculated from the inverse Chi-squared distribution using the desired probability level and degrees of freedom.
 - The failure rate is then calculated from the Chi-square value:

$$\text{Failure Rate} = \frac{x^2 \cdot 10^9}{2 (\text{A.F.} * \text{Device Hours})}$$

where x^2 = Chi-Squared value at 60% confidence level and $(2f + 2)$ degrees of freedom,

where f is the number of failures, Device Hours = (No. of Devices) * (No. of Hours)

- The Acceleration Factor (A.F.) is calculated using Arrhenius relationship.

$$\text{Acceleration Factor} = \text{Exp} \{ (E_a/k) \times (1/T_{use} - 1/T_{stress}) \}$$

Where:

E_a = Activation Energy (eV), assumed 0.7 eV

k = Boltzmann's constant (8.617×10^{-5} eV/ $^\circ\text{K}$)

T_{stress} = Temperature at accelerated conditions in degrees Kelvin ($^\circ\text{K} = 125^\circ\text{C} + 273.16$)

T_{use} = Temperature at normal use conditions in degrees Kelvin ($^\circ\text{K} = 55^\circ\text{C} + 273.16$)

A.F. = Acceleration Factor

4.0 Silicon Reliability Summary

Using the above mentioned methodology, summary of failure rates for various process nodes (with active products) are as shown below,

Table 4.0.1: High Temperature Operational Life Test/Burn In (HTOL/BI)

Foundry Process	Total Units	Failures	Total Device Hours	FIT Rate
0.18um (Global Foundries)	1128	0	3098869	3.7937
0.18um (Jazz)	154	0	438946	26.7828
0.35um (Dongbu)	750	0	2965434	3.9644
0.35um (Magnachip)	3526	0	2925027	4.0191
0.35um (XFAB)	1417	0	2073400	5.67
0.50um (Magnachip)	796	0	656364	17.9111
0.5um (Excel Power)	150	0	68935	170.5413
0.5um (Jazz)	450	0	379996	30.9377
0.6um (XFAB)	1952	0	1698937	6.9197
0.8um (XFAB)	879	0	593872	19.7958
1.0um (Excel Power)	200	0	164916	71.2862
1.0um (XFAB)	519	0	1193000	9.8543
1.4um (Microsemi GG)	200	0	150213	78.2638
2.0um (Microsemi GG)	50	0	30738	382.4603
3.0um (Microsemi GG)	349	0	88399	132.9911
6.0um (Microsemi GG)	400	0	408490	28.7797

Notes:

1. FIT rates are calculated based on 0.7ev, 60% confidence level & Tj = 55C
2. Total device hours are normalized to Tj = 125C

Table 4.0.2: Early Life Failure Rate (ELFR)

Product	Foundry	Process Node	Conditions	Units	Failures	Device Hours
LX82XX	Global Foundries	0.18um	125C @ 48hrs	2400	0	115200
LX82XX	Global Foundries	0.18um	150C @ 48hrs	4800	0	230400
Total =				7200	0	345600

Table 4.0.3: High Temperature Storage Life (HTSL) – Wafer level

Product	Package	Condition	Hours	Wafers	Failures	Wafer Hours
AAP8XX	8 pin SB	150C	1000	1	0	1000
AAP8XX	8 pin SB	150C	1000	1	0	1000
AAP1XX	Bump Die	150C	1000	1	0	1000
Total =				3	0	3000

Additional wafer level reliability data (like GOI, TDDB, EM, etc) is maintained by the foundry as applicable per their internal ongoing monitoring program.

4.1 ESD Summary

Table 4.1.1: ESD Summary (Data from HBM, CDM & MM models as applicable)

Process/Foundry	Product	HBM	CDM	MM
0.18um Global Foundries	LX82XX	4000V	2000V	150V
0.18um Global Foundries	LX82XX	2000V	2000V	
0.18um Global Foundries	LX24XX	8000V	2000V	
0.18um Global Foundries	LX24XX	1500V	2000V	
0.18um Jazz	LX24XXAVIG	8000V	2000V	2000V
0.35um Dongbu	LX65XX	5000V	700V	200V
0.35um Dongbu	LX19XX	5000V	1500V	250V
0.35um Magnachip	LX71XX	500V		
0.35um Magnachip	LX13XXX	1000V		
0.35um Magnachip	LX22XX	1000V	500V	150V
0.35um Magnachip	LX23XXX	3000V	1500V	200V
0.35um Magnachip	LX23XXX	4000V	2000V	350V
0.35um Magnachip	LX24XXX	5000V	2000V	250V
0.35um Magnachip	LX24XXX	6000V	2000V	250V
0.35um Magnachip	LX65XX	3000V	2000V	300V
0.35um Magnachip	LX71XX	600V	2000V	
0.35um Magnachip	LX71XX	1000V	750V	25V
0.35um Magnachip	LX71XX	2000V	2000V	250V
0.35um Magnachip	LX71XX	2500V	2000V	200V
0.35um Magnachip	LX71XX	1500V	1500V	100V
0.35um Magnachip	LX71XX	1500V	2000V	75V
0.35um Magnachip	LX71XX	2000V	2000V	50V
0.35um Magnachip	LX71XX	1500V	1500V	
0.35um Magnachip	LX73XX	1000V	2000V	100V

0.35um Magnachip	LX82XX	5000V	2000V	150V
0.35um Magnachip	LX27XXX	3000V	2000V	
0.35um XFAB	AA6XX	1000		
0.35um XFAB	AA5XX	1000V		
0.35um XFAB	LX23XXX	1500V	1500V	350V
0.50um Excel Power	LX82XX	1500V	2000V	200
0.35um XFAB	AAP8XX	150V (i/p to gnd; 2000V (FB1, FB2 & HPF to gnd) & 7500V (o/p to gnd)		
0.35um XFAB	LX33XX	2000V	750V corner pins, 500V all other pins	
0.50um Jazz	LX13XXX	5500V	1500	500V
0.50um Jazz	LX73XX	1500V	1000V	100V
0.50um Jazz	LX96XX	3500V	2000V	200V
0.50um Magnachip	NX41XX	1000V	500V	
0.60um XFAB	LX27XX	1000V		
0.60um XFAB	NX95XX	500V	2000V	50V
0.60um XFAB	LX65XX	3500V	1500V	250V
0.60um XFAB	LX17XX		1000V	
0.60um XFAB	LX27XXX	5000V	2000V	200V
0.60um XFAB	LX27XXX	4000V	2000V	150V
0.80um XFAB	LX65XX	4000V	1500V	250V
1.0um Excel Power	LX65XX	3500V	1500V	250V
6.0um Microsemi GG	LX23XXX	4000V		
6.0um Microsemi GG	LX23XXX	4000V		
6.0um Microsemi GG	LX23XXX	4000V		

6.0 Package Reliability Summary

Package level data is provided below in the following categories

- By package
- By products (currently supported)

6.1 Package Reliability (By Package)

Table 6.1.1: Power Temp Cycles (PTC)

Package	Conditions	Cycles	Units	Failures	Device Cycles
LGA	-65 to 150C	2000	50	0	100000
LFGA	-40 to 125C	1000	50	0	50000
QFN	-65 to 150C	1000	50	0	50000
Module	-65 to 150C	1000	50	0	50000
QFN	-40 to 85C	1000	25	0	25000
Total =			225	0	275000

Table 6.1.2: High Temperature Storage Life (HTSL)

Package	Temperature	Hours	Units	Failures	Device Hours
DFN	150	100	25	0	2500
		1000	554	0	554000
LFGA	130	1000	75	0	75000
	150	1000	45	0	45000
LGA	150	1000	50	0	50000
Microphone Carrier Board	150	1000	45	0	45000
QFN	150	1000	170	0	170000
QFN (FC)	150	1000	404	0	404000
QSOP	150	1000	50	0	50000
	175	1000	231	0	231000
SOIC (NB)	150	1000	75	0	75000
SOIC (WB)	150	1000	50	0	50000
WLCSP	150	1000	50	0	50000
TSSOP	175	1000	122	0	122000
Total =			1946	0	1923500

Table 6.1.8: Temperature Cycles (TC)

Package	Conditions	Cycles	Units	Failures	Device Cycles
Ceramic SOIC	method 1010, condition C	100	30	0	3000
CERDIP	-65C to +150C	100	150	0	15000
CQFP	method 1010, condition C	100	15	0	1500
DFN	-65C to +150C	100	700	0	70000
		500	700	0	350000
		1000	154	0	154000
LFGA	-65C to +150C	500	154	0	77000
LGA	-65C to +150C	500	50	0	25000
		1000	150	0	150000
Module	-65C to +150C	500	50	0	25000
MSOP	-40C to +100C	100	400	0	40000
	-65C to +150C	100	50	0	5000
PDIP	-65C to +150C	100	50	0	5000
Plastic 1206	-40C to +100C	100	49	0	4900
PLCC	-65C to +150C	100	50	0	5000
QFN	-55C to +125C	700	75	0	52500
	-65C to +150C	100	898	0	89800
		500	224	0	112000
		100	50	0	5000
QFN (FC)	-65C to +150C	500	300	0	150000
		1000	308	0	308000
QSOP	-65C to +150C	100	100	0	10000
		500	100	0	50000
		100	22	0	2200
	JESD22-A104-B	500	45	0	22500
	-65C to 175C	500	231	0	115500
SC70	-65C to +150C	100	50	0	5000
SOIC (NB)	-65C to +150C	100	1050	0	105000
		250	25	0	6250
		500	50	0	25000
SOIC (WB)	-65C to +150C	100	300	0	30000
		500	50	0	25000
SOT 23	-65C to +150C	100	50	0	5000

SSOP	-65C to +150C	100	101	0	10100
TO 220	-65C to +150C	100	100	0	10000
TSOT	-65C to +150C	100	100	0	10000
TSOT 23	-65C to +150C	100	149	0	14900
TSSOP	-55C to +150C	2000	77	0	154000
	-65C to +150C	100	300	0	30000
	-65C to +175C	500	231	0	115500
UDFN	-65C to +150C	100	50	0	5000
WLCSP	-40C to +125C	500	100	0	50000
	-65C to +150C	500	50	0	25000
Total =		7938	0	2473650	

Table 6.1.9: Temperature Humidity Bias (THB)

Package	Conditions	Hours	Units	Failures	Device Hours
DFN	85C/85RH	2000	198	0	198000
LGA	85C/85RH	2025	50	0	101250
Module	85C/85RH	1000	50	0	50000
QFN	130C/85RH	116	75	0	8700
	85C/85RH	1000	50	0	50000
QFN (FC)	130C/85RH	96	25	0	2400
	85C/85RH	3000	150	0	150000
QSOP	85C/85RH	1000	281	0	281000
SOIC (WB)	85C/85RH	1000	50	0	50000
SOT	85C/85RH	160	77	0	12320
TO	85C/85RH	1000	50	0	50000
WLCSP	85C/85RH	1000	50	0	50000
TSSOP	85C/85RH	1000	231	0	231000
Total =		1337	0	1234670	

SG29XXX	P-5	-65C to +150C	100	100	0	10000
SG34XX	M-8	-65C to +150C	100	50	0	5000
SG35XX	N-18	-65C to +150C	100	50	0	5000
Total =			7327	0	2340150	

Table 6.2.9: Temperature Humidity Bias (THB)

Product	Package	Conditions	Hours	Units	Failures	Device Hours
LX22XX	DB-36	85C/85RH	1000	50	0	50000
LX27XXX	DW-24	85C/85RH	1000	50	0	50000
LX71XX	LD335-12	85C/85RH	2000	100	0	100000
LX71XX	CSP216-20	85C/85RH	1000	50	0	50000
LX71XX	LD22-8	85C/85RH	2000	98	0	98000
LX71XX	LQ22-12	85C/85RH	2000	100	0	100000
LX71XX	LQ22-12	85C/85RH	1000	50	0	50000
LX73XX	LQ44-24	85C/85RH	1000	50	0	50000
LX82XX	LQ32-12	130C/85RH	96	25	0	2400
LX96XX	QFN1515-MCP	130C/85RH	116	75	0	8700
LXM24XX	LG-2	85C/85RH	2025	50	0	101250
	Module	85C/85RH	1000	50	0	50000
AA550	4LD SOT143	85C/85RH	160	77	0	12320
LX3301	14-pin TSSOP (RoHS)	85C/85RH	1000	231	0	231000
Total =			1056	0	953670	

Revision History

ECO/Change	Revision	Description of change	Date of Revision																														
01897	A	Initial Release (covering qualification data since January 2008 till August 2015)	10/23/2015																														
01939	B	Updated tables (4.0.1, 4.1.1, 6.1.2, 6.1.7, 6.1.8, 6.1.9, 6.2.2, 6.2.7, 6.2.8, 6.2.9) based on additional qualification data (from September 2015 thru December 2015)	12/17/2015																														
PD-000124027	C	Updated tables HTOL Table 4.0.1 with qualification data from March RTP and split 0.6um and 1.0um product from previous data.	4/01/2016																														
PD-000157984	D	<p>Added in Section 2.0 Product Portfolio – Hi Rel Product/Product AA7XX/AA7XX Updated qualification data in Table 4.0.1: High Temperature Operational Life Test/Burn In (HTOL/BI)</p> <table border="1"> <thead> <tr> <th>Foundry Process</th> <th>Total Units</th> <th>Failures</th> <th>Total Device Hours</th> <th>FIT Rate</th> </tr> </thead> <tbody> <tr> <td>0.18um (Global Foundries)</td> <td>820</td> <td>0</td> <td>2069801</td> <td>5.6799</td> </tr> <tr> <td>0.6um (XFAB)</td> <td>1952</td> <td>0</td> <td>1698937</td> <td>6.9197</td> </tr> <tr> <td>1.0um (XFAB)</td> <td>519</td> <td>0</td> <td>1193000</td> <td>9.8543</td> </tr> </tbody> </table> <p>Updated ESD Summary Table 4.1.1 to include LX8204 ESD ratings</p> <table border="1"> <thead> <tr> <th>0.18um Global Foundries</th> <th>LX24XX</th> <th>1500V</th> <th>2000V</th> <th></th> </tr> </thead> <tbody> <tr> <td></td> <td></td> <td></td> <td></td> <td></td> </tr> </tbody> </table> <p>Updated the following tables for LX8204 package reliability data Table 6.1.2: High Temperature Storage Life (HTSL) Table 6.1.4: Highly Accelerated Stress Test (HAST) Table 6.1.8: Temperature Cycles (TC) Table 6.2.2: High Temperature Storage Life (HTSL) Table 6.2.4: Highly Accelerated Stress Test (HAST) Table 6.2.8: Temperature Cycles (TC)</p>	Foundry Process	Total Units	Failures	Total Device Hours	FIT Rate	0.18um (Global Foundries)	820	0	2069801	5.6799	0.6um (XFAB)	1952	0	1698937	6.9197	1.0um (XFAB)	519	0	1193000	9.8543	0.18um Global Foundries	LX24XX	1500V	2000V							6/27/2016
Foundry Process	Total Units	Failures	Total Device Hours	FIT Rate																													
0.18um (Global Foundries)	820	0	2069801	5.6799																													
0.6um (XFAB)	1952	0	1698937	6.9197																													
1.0um (XFAB)	519	0	1193000	9.8543																													
0.18um Global Foundries	LX24XX	1500V	2000V																														
PD-000161627	E	<p>Updated the following tables for LX3302QPW, LX7165-X5 V2R1, LX8237 V3R1 and LX8237 V3R2 reliability test data:</p> <p>Table 4.0.1: High Temperature Operational Life Test/Burn In (HTOL/BI) Table 4.1.1: ESD Summary (Data from HBM, CDM & MM models as applicable) Table 5.1: Program/Erase Endurance Cycling – High temperature Table 5.2: Program/Erase Endurance Cycling – Low temperature Table 5.3: Low Temperature Data Retention Table 5.4: High Temperature Storage Table 6.1.2: High Temperature Storage Life (HTSL) Table 6.1.3: UnBiased Highly Accelerated Stress Test (UHAST) Table 6.1.4: Highly Accelerated Stress Test (HAST) Table 6.1.8: Temperature Cycles (TC) Table 6.2.2: High Temperature Storage Life (HTSL) Table 6.2.3: UnBiased Highly Accelerated Stress Test (UHAST) Table 6.2.4: Highly Accelerated Stress Test (HAST) Table 6.2.8: Temperature Cycles (TC)</p>	10/24/16																														